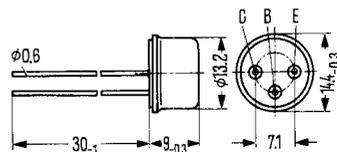


## PNP Transistors for AF output stages and switching applications

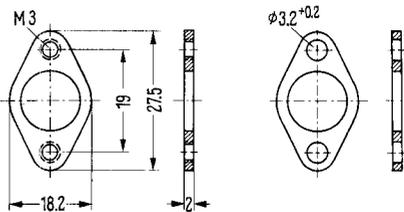
Not for new development

TF 78/30 and TF 78/60 are alloyed PNP germanium transistors in cases 8 A 3 DIN 41878 (sim. TO-8). The terminals are electrically insulated from the case. For mounting the transistors on a chassis, mounting parts Q 62901-B 2-A and Q 62901-B 2-B are available, to be ordered separately. TF 78/30 and TF 78/60 are designed for AF power stages and for switching applications; for use in push-pull power stages, the transistors TF 78/30 are also available in pairs.

Type	Order number
TF 78/30 II	Q 62606-X 3078-X 2
TF 78/30 III	Q 62606-X 3078-X 3
TF 78/30 IV	Q 62606-X 3078-X 4
TF 78/30 V	Q 62606-X 3078-X 5
TF 78/30 paired	Q 62606-P 3078
TF 78/60 II	Q 62606-X 6078-X 2
TF 78/60 III	Q 62606-X 6078-X 3
TF 78/60 IV	Q 62606-X 6078-X 4
TF 78/60 V	Q 62606-X 6078-X 5
Tensioning plate washer	Q 62901-B 2-A Q 62901-B 2-B



Weight approx. 5.5 g Dimensions in mm



Part A: Tensioning plate

Part B: Washer

### Maximum ratings

	TF 78/30	TF 78/60		
Collector-emitter voltage	$-V_{CE0}$	24	45	V
Collector-emitter voltage ( $V_{BE} \geq 0.25$ V)	$-V_{CEV}$	32	64	V
Collector-base voltage	$-V_{CBO}$	32	64	V
Emitter-base voltage	$-V_{EBO}$	10	16	V
Collector current	$-I_C$	600	600	mA
Base current	$-I_B$	100	100	mA
Junction temperature	$T_j$	90	90	$^{\circ}$ C
Storage temperature	$T_s$	-30 to +75	-30 to +75	$^{\circ}$ C
Total power dissipation ( $T_{case} \leq 45$ $^{\circ}$ C)	$P_{tot}$	3	3	W

### Thermal resistance

Junction to ambient air	$R_{thJamb}$	$\leq 120$	$\leq 120$	K/W
Junction to case	$R_{thJcase}$	$\leq 15$	$\leq 15$	K/W

Not for new development

**Static characteristics** ( $T_{case} = 25\text{ }^\circ\text{C}$ )

The transistors TF 78/30 and TF 78/60 are classified in groups of static forward current transfer ratio  $h_{FE}$  at  $-I_C = 50\text{ mA}$ , which are indicated by Roman numerals. The following values apply at a collector voltage of  $-V_{CE} = 0.7\text{ V}$  and the following collector currents.

II		III	IV	V	$h_{FE}$ group
$-I_C$ mA	$h_{FE}$ $I_C/I_B$	$h_{FE}$ $I_C/I_B$	$h_{FE}$ $I_C/I_B$	$h_{FE}$ $I_C/I_B$	$V_{BE}$ V
50	38 (30 to 45)*	56 (45 to 67)*	83 (67 to 100)*	125 (100 to 150)*	0.27 (<0.45)
200	35	52	77	116	0.41 (<0.65)
500	25	37	55	83	0.54 (<1.0)

Collector saturation voltage for the characteristics which pass the operating points stated below:

- $-V_{CE} = 0.7\text{ V}; -I_C = 50\text{ mA}$
- $-V_{CE} = 0.7\text{ V}; -I_C = 200\text{ mA}$
- $-V_{CE} = 0.7\text{ V}; -I_C = 500\text{ mA}$

TF 78/30, TF 78/60		
$-V_{CEsat}$	0.19 (<0.3)	V
$-V_{CEsat}$	0.21 (<0.4)	V
$-V_{CEsat}$	0.26 (<0.5)	V

**Cutoff currents**

- Collector-emitter cutoff current ( $-V_{CEV}^1$ )
- Collector-base cutoff current ( $-V_{CBO}^1$ )
- Collector-emitter cutoff current ( $-V_{CEO} = 5\text{ V}$ )
- Emitter-base cutoff current ( $-V_{EBO}^1$ )

$-I_{CEV}$	10 (<30)*	$\mu\text{A}$
$-I_{CBO}$	10 (<30)	$\mu\text{A}$
$-I_{CEO}$	200	$\mu\text{A}$
$-I_{EBO}$	8 (<30)*	$\mu\text{A}$

**Dynamic characteristics** ( $T_{case} = 25\text{ }^\circ\text{C}$ )

- Test conditions:  $-I_C = 5\text{ mA}; -V_{CE} = 5\text{ V}$
- Cutoff frequency in common emitter circuit
- Cutoff frequency in common base circuit
- Base series resistance
- Collector junction capacitance

$f_x$	12	kHz
$f_\beta$	700	kHz
$r_{bb'}$	50	$\Omega$
$C_{b'c}$	70	pf

**Four-terminal characteristics**

- Test condition:  $-I_C = 5\text{ mA}; -V_{CE} = 5\text{ V}; f = 1\text{ kHz}$

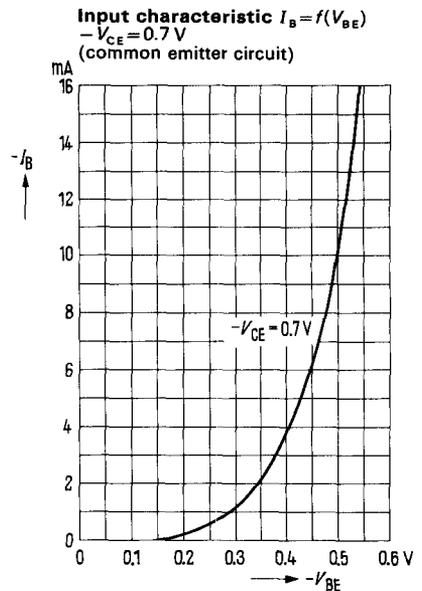
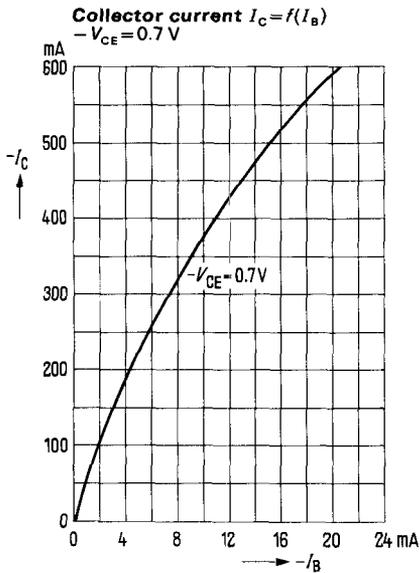
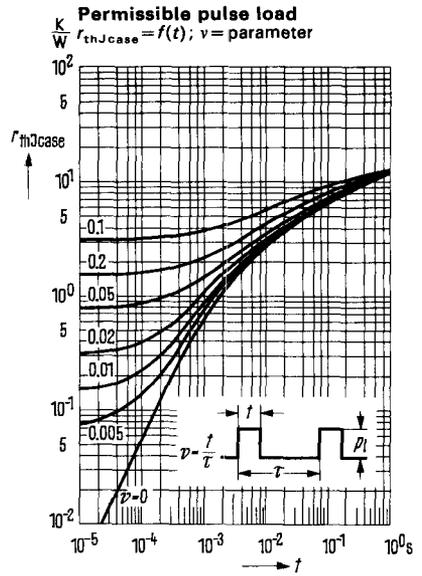
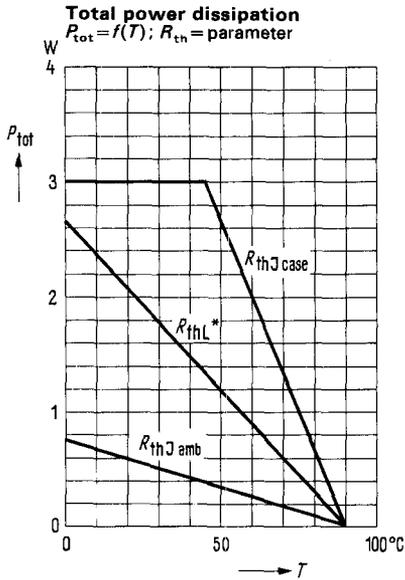
$h_{11e}$	350	$\Omega$
$h_{12e}$	6	$\cdot 10^4$
$h_{21e}$	45	-
$h_{22e}$	100	$\mu\text{mhos}$
$Y_{21e}$	127	mmhos

**Switching times**

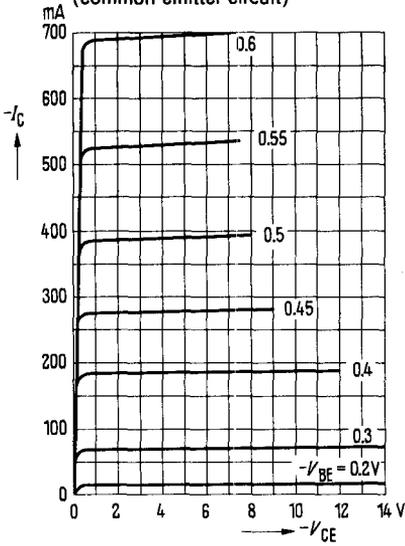
At an overdriving factor of  $\ddot{u} = 1.5$  to 3 and a "turn-off" base current of  $I_{B2} = 3.3\text{ mA}$  ( $-I_C = 200\text{ mA}$ ) the following switching times apply:

$t_{on}$	6 (<12)	$\mu\text{s}$
$t_s$	4 (<10)	$\mu\text{s}$
$t_f$	18 (<36)	$\mu\text{s}$

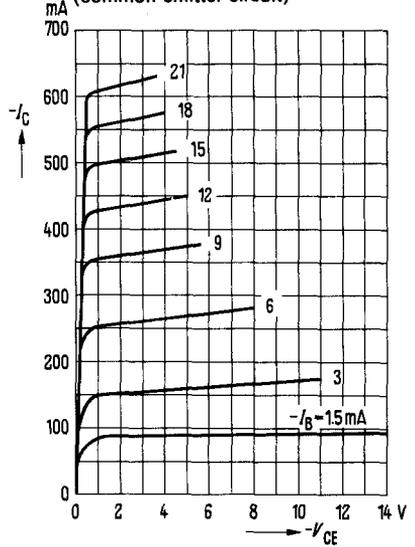
<sup>1)</sup> See maximum ratings  
<sup>\*</sup> AQL = 0.65%



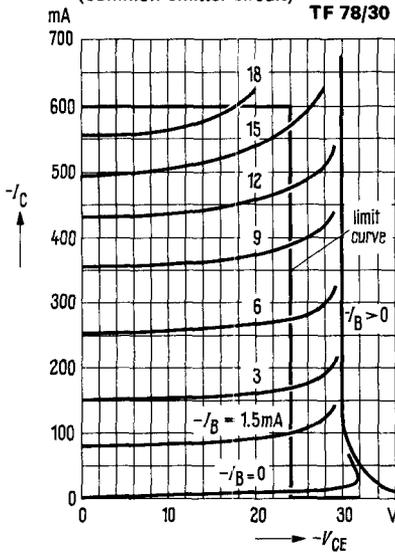
**Output characteristics  $I_C = f(V_{CE})$**   
 $-V_{BE}$  = parameter  
 (common emitter circuit)



**Output characteristics  $I_C = f(V_{CE})$**   
 $-I_B$  = parameter  
 (common emitter circuit)



**Output characteristics and limit curve for switching operation  $I_C = f(V_{CE})$**   
 (common emitter circuit)



**Output characteristics and limit curve for switching operation  $I_C = f(V_{CE})$**   
 (common emitter circuit)

